

Hongqi Xu

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

252
papers

10,468
citations

48
h-index

96
g-index

276
ext. papers

11,618
ext. citations

5.3
avg, IF

6.24
L-index

#	Paper	IF	Citations
252	Measurements of anisotropic g-factors for electrons in InSb nanowire quantum dots. <i>Nanotechnology</i> , 2021 , 32, 020002	3.4	1
251	Adiabatic topological pumping in a semiconductor nanowire. <i>Journal of Applied Physics</i> , 2021 , 130, 174301	15	0
250	Strong and tunable spin-orbit interaction in a single crystalline InSb nanosheet. <i>Npj 2D Materials and Applications</i> , 2021 , 5,	8.8	6
249	A highly tunable quadruple quantum dot in a narrow bandgap semiconductor InAs nanowire. <i>Nanoscale</i> , 2021 , 13, 3983-3990	7.7	3
248	A charge sensor integration to tunable double quantum dots on two neighboring InAs nanowires. <i>Nanoscale</i> , 2021 , 13, 1048-1054	7.7	2
247	Topological states and interplay between spin-orbit and Zeeman interactions in a spinful Su-Schrieffer-Heeger nanowire. <i>Physical Review B</i> , 2021 , 104,	3.3	1
246	Josephson junctions in double nanowires bridged by in-situ deposited superconductors. <i>Physical Review Research</i> , 2021 , 3,	3.9	3
245	Measurements of spin-orbit interaction in epitaxially grown InAs nanosheets. <i>Applied Physics Letters</i> , 2020 , 117, 132101	3.4	2
244	Transport signatures of relativistic quantum scars in a graphene cavity. <i>Physical Review B</i> , 2020 , 101,	3.3	2
243	Evidence of half-integer Shapiro steps originated from nonsinusoidal current phase relation in a short ballistic InAs nanowire Josephson junction. <i>Physical Review Research</i> , 2020 , 2,	3.9	4
242	Detection of charge states of an InAs nanowire triple quantum dot with an integrated nanowire charge sensor. <i>Applied Physics Letters</i> , 2020 , 117, 262102	3.4	1
241	Observation and Ultrafast Dynamics of Inter-Sub-Band Transition in InAs Twinning Superlattice Nanowires. <i>Advanced Materials</i> , 2020 , 32, e2004120	24	6
240	Ambipolar transport in narrow bandgap semiconductor InSb nanowires. <i>Nanoscale</i> , 2020 , 12, 8159-8165	7.7	2
239	A Force-Engineered Lint Roller for Superclean Graphene. <i>Advanced Materials</i> , 2019 , 31, e1902978	24	31
238	A Single-Electron Transistor Made of a 3D Topological Insulator Nanoplate. <i>Advanced Materials</i> , 2019 , 31, e1903686	24	5
237	Dominant nonlocal superconducting proximity effect due to electron-electron interaction in a ballistic double nanowire. <i>Science Advances</i> , 2019 , 5, eaaw2194	14.3	12
236	Gate defined quantum dot realized in a single crystalline InSb nanosheet. <i>Applied Physics Letters</i> , 2019 , 114, 023108	3.4	5

235	Mott variable-range hopping transport in a MoS nanoflake.. <i>RSC Advances</i> , 2019 , 9, 17885-17890	3.7	14
234	Coexistence of induced superconductivity and quantum Hall states in InSb nanosheets. <i>Physical Review B</i> , 2019 , 99,	3.3	6
233	Universal conductance fluctuations and phase-coherent transport in a semiconductor BiOSe nanoplate with strong spin-orbit interaction. <i>Nanoscale</i> , 2019 , 11, 10622-10628	7.7	9
232	Towards super-clean graphene. <i>Nature Communications</i> , 2019 , 10, 1912	17.4	89
231	Measurements of Strain and Bandgap of Coherently Epitaxially Grown Wurtzite InAsP-InP Core-Shell Nanowires. <i>Nano Letters</i> , 2019 , 19, 2674-2681	11.5	11
230	Coulomb blockade from the shell of an InP-InAs core-shell nanowire with a triangular cross section. <i>Applied Physics Letters</i> , 2019 , 114, 053108	3.4	7
229	Nitrogen cluster doping for high-mobility/conductivity graphene films with millimeter-sized domains. <i>Science Advances</i> , 2019 , 5, eaaw8337	14.3	39
228	Growth Mechanism of SmB Nanowires Synthesized by Chemical Vapor Deposition: Catalyst-Assisted and Catalyst-Free. <i>Nanomaterials</i> , 2019 , 9,	5.4	2
227	Synthesis Of Samarium Oxychloride Nanoplates By Chemical Vapour Deposition. <i>Journal of Experimental Nanoscience</i> , 2019 , 14, 33-40	1.9	1
226	Revealing misfit dislocations in InAs P -InP core-shell nanowires by x-ray diffraction. <i>Nanotechnology</i> , 2019 , 30, 505703	3.4	7
225	Dimension Engineering of High-Quality InAs Nanostructures on a Wafer Scale. <i>Nano Letters</i> , 2019 , 19, 1632-1642	11.5	22
224	Crossover from Coulomb blockade to ballistic transport in InAs nanowire devices. <i>Nanotechnology</i> , 2019 , 30, 124001	3.4	3
223	Two-Dimensional Quantum Transport in Free-Standing InSb Nanosheets. <i>Nano Letters</i> , 2019 , 19, 561-569	11.5	17
222	Supercurrent and Multiple Andreev Reflections in InSb Nanosheet SNS Junctions. <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1800538	1.3	6
221	Charge transport and electron-hole asymmetry in low-mobility graphene/hexagonal boron nitride heterostructures. <i>Journal of Applied Physics</i> , 2018 , 123, 064303	2.5	1
220	Strong spin-orbit interaction and magnetotransport in semiconductor BiOSe nanoplates. <i>Nanoscale</i> , 2018 , 10, 2704-2710	7.7	37
219	Low-field magnetotransport in graphene cavity devices. <i>Nanotechnology</i> , 2018 , 29, 205707	3.4	1
218	Tunable Low Loss 1D Surface Plasmons in InAs Nanowires. <i>Advanced Materials</i> , 2018 , 30, e1802551	24	11

217	Anisotropic Pauli Spin-Blockade Effect and Spin-Orbit Interaction Field in an InAs Nanowire Double Quantum Dot. <i>Nano Letters</i> , 2018 , 18, 4741-4747	11.5	16
216	Anomalous modulation of Josephson radiation in nanowire-based Josephson junctions. <i>Physical Review B</i> , 2018 , 98,	3.3	5
215	Cooper-pair splitting in two parallel InAs nanowires. <i>New Journal of Physics</i> , 2018 , 20, 063021	2.9	18
214	Low-Temperature and Rapid Growth of Large Single-Crystalline Graphene with Ethane. <i>Small</i> , 2018 , 14, 1702916	11	30
213	Signature of quantum Griffiths singularity state in a layered quasi-one-dimensional superconductor. <i>Nature Communications</i> , 2018 , 9, 4656	17.4	17
212	Applied Stress-Assisted Growth of Single Crystal FeO Nanowires. <i>Nanomaterials</i> , 2018 , 8,	5.4	2
211	Ballistic transport and quantum interference in InSb nanowire devices. <i>Chinese Physics B</i> , 2017 , 26, 027305	0.5	4
210	Epitaxial Growth of Ternary Topological Insulator Bi Te Se 2D Crystals on Mica. <i>Small</i> , 2017 , 13, 1603572	11	16
209	Electron-Hole Symmetry Breaking in Charge Transport in Nitrogen-Doped Graphene. <i>ACS Nano</i> , 2017 , 11, 4641-4650	16.7	31
208	Coherent Transport in a Linear Triple Quantum Dot Made from a Pure-Phase InAs Nanowire. <i>Nano Letters</i> , 2017 , 17, 4158-4164	11.5	13
207	High electron mobility and quantum oscillations in non-encapsulated ultrathin semiconducting BiOSe. <i>Nature Nanotechnology</i> , 2017 , 12, 530-534	28.7	332
206	Synthesis of BiTe Nanotubes Using Te Nanotubes as a Template. <i>Journal of Nanoscience and Nanotechnology</i> , 2017 , 17, 741-48	1.3	2
205	Phase transition in hybrid superconductor InSb nanowire quantum dot devices. <i>Physical Review B</i> , 2017 , 95,	3.3	24
204	Majorana fermions in topological-insulator nanowires: From single superconducting nanowires to Josephson junctions. <i>Physical Review B</i> , 2017 , 95,	3.3	6
203	Wrinkle-Free Single-Crystal Graphene Wafer Grown on Strain-Engineered Substrates. <i>ACS Nano</i> , 2017 , 11, 12337-12345	16.7	112
202	Growth of InAs NWs with controlled morphology by CVD. <i>Journal of Physics: Conference Series</i> , 2017 , 864, 012013	0.3	
201	InAs/GaSb core-shell nanowires grown on Si substrates by metal-organic chemical vapor deposition. <i>Journal of Physics: Conference Series</i> , 2017 , 864, 012001	0.3	
200	Extracting band structure characteristics of GaSb/InAs core-shell nanowires from thermoelectric properties. <i>Physical Review B</i> , 2017 , 95,	3.3	5

199	Gate tunable parallel double quantum dots in InAs double-nanowire devices. <i>Applied Physics Letters</i> , 2017 , 111, 233513	3.4	5
198	Surface Monocrystallization of Copper Foil for Fast Growth of Large Single-Crystal Graphene under Free Molecular Flow. <i>Advanced Materials</i> , 2016 , 28, 8968-8974	24	110
197	Coherent Charge Transport in Ballistic InSb Nanowire Josephson Junctions. <i>Scientific Reports</i> , 2016 , 6, 24822	4.9	21
196	Measurements of the spin-orbit interaction and Landé factor in a pure-phase InAs nanowire double quantum dot in the Pauli spin-blockade regime. <i>Applied Physics Letters</i> , 2016 , 109, 053106	3.4	15
195	Schottky barrier and contact resistance of InSb nanowire field-effect transistors. <i>Nanotechnology</i> , 2016 , 27, 275204	3.4	10
194	Growth of High Material Quality Group III-Antimonide Semiconductor Nanowires by a Naturally Cooling Process. <i>Nanoscale Research Letters</i> , 2016 , 11, 222	5	4
193	Covalently bonded single-molecule junctions with stable and reversible photoswitched conductivity. <i>Science</i> , 2016 , 352, 1443-5	33.3	529
192	Free-Standing Two-Dimensional Single-Crystalline InSb Nanosheets. <i>Nano Letters</i> , 2016 , 16, 834-41	11.5	59
191	Surface Engineering of Copper Foils for Growing Centimeter-Sized Single-Crystalline Graphene. <i>ACS Nano</i> , 2016 , 10, 2922-9	16.7	78
190	Weak antilocalization and electron-electron interaction in coupled multiple-channel transport in a Bi ₂ Se ₃ thin film. <i>Nanoscale</i> , 2016 , 8, 1879-85	7.7	40
189	Probe of local impurity states by bend resistance measurements in graphene cross junctions. <i>Nanotechnology</i> , 2016 , 27, 245204	3.4	2
188	Generic technique to grow III-V semiconductor nanowires in a closed glass vessel. <i>AIP Advances</i> , 2016 , 6, 065311	1.5	1
187	k.p theory of freestanding narrow band gap semiconductor nanowires. <i>AIP Advances</i> , 2016 , 6, 125109	1.5	13
186	Electronic Structures of Free-Standing Nanowires made from Indirect Bandgap Semiconductor Gallium Phosphide. <i>Scientific Reports</i> , 2016 , 6, 28240	4.9	10
185	Schottky barrier heights at the interfaces between pure-phase InAs nanowires and metal contacts. <i>Journal of Applied Physics</i> , 2016 , 119, 054304	2.5	15
184	Band-inverted gaps in InAs/GaSb and GaSb/InAs core-shell nanowires. <i>Scientific Reports</i> , 2016 , 6, 38698	4.9	7
183	Electronic structures of [1 1 1]-oriented free-standing InAs and InP nanowires. <i>Journal of Physics Condensed Matter</i> , 2016 , 28, 135303	1.8	6
182	InAs/GaSb core-shell nanowires grown on Si substrates by metal-organic chemical vapor deposition. <i>Nanotechnology</i> , 2016 , 27, 275601	3.4	15

181	Patterning two-dimensional chalcogenide crystals of Bi ₂ Se ₃ and In ₂ Se ₃ and efficient photodetectors. <i>Nature Communications</i> , 2015 , 6, 6972	17.4	133
180	Phase-coherent transport and spin relaxation in InAs nanowires grown by molecule beam epitaxy. <i>Applied Physics Letters</i> , 2015 , 106, 173105	3.4	19
179	Formation of long single quantum dots in high quality InSb nanowires grown by molecular beam epitaxy. <i>Nanoscale</i> , 2015 , 7, 14822-8	7.7	17
178	Nanoscale opening fabrication on Si (111) surface from SiO ₂ barrier for vertical growth of III-V nanowire arrays. <i>Nanotechnology</i> , 2015 , 26, 265302	3.4	3
177	Growth of InAs nanowires with the morphology and crystal structure controlled by carrier gas flow rate. <i>Journal of Crystal Growth</i> , 2015 , 430, 87-92	1.6	5
176	Transport studies of electron-hole and spin-orbit interaction in GaSb/InAsSb core-shell nanowire quantum dots. <i>Physical Review B</i> , 2015 , 91,	3.3	21
175	Electronic structures of [001]- and [111]-oriented InSb and GaSb free-standing nanowires. <i>Journal of Applied Physics</i> , 2015 , 118, 094308	2.5	9
174	Interface engineering of electronic properties of graphene/boron nitride lateral heterostructures. <i>2D Materials</i> , 2015 , 2, 041001	5.9	34
173	Parity independence of the zero-bias conductance peak in a nanowire based topological superconductor-quantum dot hybrid device. <i>Scientific Reports</i> , 2014 , 4, 7261	4.9	62
172	Gate tunable nonlinear rectification effects in three-terminal graphene nanojunctions. <i>Nanoscale</i> , 2014 , 6, 4527-31	7.7	8
171	Room-temperature near-infrared photodetectors based on single heterojunction nanowires. <i>Nano Letters</i> , 2014 , 14, 694-8	11.5	118
170	Synthesis of indium nanostructure-laces by multi-step Glancing Angle Deposition. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2014 , 60, 70-74	3	6
169	Electrical characteristics of field-effect transistors based on indium arsenide nanowire thinner than 10 nm. <i>Applied Physics Letters</i> , 2014 , 105, 143101	3.4	19
168	Tunnel spectroscopy of Majorana bound states in topological superconductor/quantum dot Josephson junctions. <i>Physical Review B</i> , 2014 , 90,	3.3	10
167	Charge transport in InAs nanowire Josephson junctions. <i>Physical Review B</i> , 2014 , 89,	3.3	41
166	Suspended InAs nanowire gate-all-around field-effect transistors. <i>Applied Physics Letters</i> , 2014 , 105, 113106	3.4	25
165	Quantized conductance and its correlation to the supercurrent in a nanowire connected to superconductors. <i>Nano Letters</i> , 2013 , 13, 3614-7	11.5	25
164	Tunable zero-field Kondo splitting in a quantum dot. <i>Physical Review B</i> , 2013 , 88,	3.3	3

163	Photoelectrical response of hybrid graphene-PbS quantum dot devices. <i>Applied Physics Letters</i> , 2013 , 103, 143119	3.4	48
162	Synthesis, properties, and top-gated metal oxide semiconductor field-effect transistors of p-type GaSb nanowires. <i>RSC Advances</i> , 2013 , 3, 19834	3.7	12
161	Structural and optical properties of self-catalytic GaAs:Mn nanowires grown by molecular beam epitaxy on silicon substrates. <i>Nanoscale</i> , 2013 , 5, 7410-8	7.7	17
160	InP nanowire array solar cells achieving 13.8% efficiency by exceeding the ray optics limit. <i>Science</i> , 2013 , 339, 1057-60	33.3	962
159	Optical far-field method with subwavelength accuracy for the determination of nanostructure dimensions in large-area samples. <i>Nano Letters</i> , 2013 , 13, 2662-7	11.5	13
158	Superconductor-nanowire devices from tunneling to the multichannel regime: Zero-bias oscillations and magnetoconductance crossover. <i>Physical Review B</i> , 2013 , 87,	3.3	576
157	Nonlinear thermovoltage and thermocurrent in quantum dots. <i>New Journal of Physics</i> , 2013 , 15, 105011	2.9	89
156	Efficient light management in vertical nanowire arrays for photovoltaics. <i>Optics Express</i> , 2013 , 21 Suppl 3, A558-75	3.3	117
155	Anomalous zero-bias conductance peak in a Nb-InSb nanowire-Nb hybrid device. <i>Nano Letters</i> , 2012 , 12, 6414-9	11.5	1210
154	High critical-current superconductor-InAs nanowire-superconductor junctions. <i>Nano Letters</i> , 2012 , 12, 5622-5	11.5	29
153	Supercurrent and multiple Andreev reflections in an InSb nanowire Josephson junction. <i>Nano Letters</i> , 2012 , 12, 228-33	11.5	73
152	Colorful InAs nanowire arrays: from strong to weak absorption with geometrical tuning. <i>Nano Letters</i> , 2012 , 12, 1990-5	11.5	87
151	Drastically increased absorption in vertical semiconductor nanowire arrays: A non-absorbing dielectric shell makes the difference. <i>Nano Research</i> , 2012 , 5, 863-874	10	27
150	Excitations of surface plasmon polaritons in double layer metal grating structures. <i>Applied Physics Letters</i> , 2012 , 100, 091111	3.4	12
149	Elastic and piezoelectric properties of zincblende and wurtzite crystalline nanowire heterostructures. <i>Advanced Materials</i> , 2012 , 24, 4692-706	24	45
148	Lineshape of the thermopower of quantum dots. <i>New Journal of Physics</i> , 2012 , 14, 033041	2.9	59
147	Valley-dependent Brewster angles and Goos-Hänchen effect in strained graphene. <i>Physical Review Letters</i> , 2011 , 106, 176802	7.4	210
146	Memristive and Memcapacitive Characteristics of a Au/TiO ₂ /InP/InGaAs Diode. <i>IEEE Electron Device Letters</i> , 2011 , 32, 131-133	4.4	24

145	Efficient methods of nanoimprint stamp cleaning based on imprint self-cleaning effect. <i>Nanotechnology</i> , 2011 , 22, 185301	3.4	5
144	Fabrication and characterization of bilayer metal wire-grid polarizer using nanoimprint lithography on flexible plastic substrate. <i>Microelectronic Engineering</i> , 2011 , 88, 3108-3112	2.5	32
143	InSb Nanowire Field-Effect Transistors and Quantum-Dot Devices. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011 , 17, 907-914	3.8	30
142	Scattering matrix method for optical excitation of surface plasmons in metal films with periodic arrays of subwavelength holes. <i>Physical Review B</i> , 2011 , 83,	3.3	38
141	Supercurrent through InAs nanowires with highly transparent superconducting contacts. <i>Nanotechnology</i> , 2011 , 22, 445701	3.4	22
140	Charge state readout and hyperfine interaction in a few-electron InGaAs double quantum dot. <i>Physical Review B</i> , 2011 , 83,	3.3	7
139	Signatures of Wigner localization in epitaxially grown nanowires. <i>Physical Review B</i> , 2011 , 83,	3.3	26
138	GaSb nanowire single-hole transistor. <i>Applied Physics Letters</i> , 2011 , 99, 262104	3.4	31
137	Correlation-induced conductance suppression at level degeneracy in a quantum dot. <i>Physical Review Letters</i> , 2010 , 104, 186804	7.4	47
136	Field-orientation dependence of the Zeeman spin splitting in (In,Ga)As quantum point contacts. <i>Physical Review B</i> , 2010 , 81,	3.3	17
135	Gate-defined double quantum dot with integrated charge sensors realized in InGaAs/InP by incorporating a high- ϵ dielectric. <i>Applied Physics Letters</i> , 2010 , 96, 162107	3.4	9
134	Nonlinear electrical properties of Si three-terminal junction devices. <i>Applied Physics Letters</i> , 2010 , 97, 242106	3.4	15
133	Coupling of light into nanowire arrays and subsequent absorption. <i>Journal of Nanoscience and Nanotechnology</i> , 2010 , 10, 7183-7	1.3	74
132	Magnetic barrier on strained graphene: A possible valley filter. <i>Physical Review B</i> , 2010 , 82,	3.3	116
131	Probing strain in bent semiconductor nanowires with Raman spectroscopy. <i>Nano Letters</i> , 2010 , 10, 1280-1285	6.5	79
130	Photovoltaics with piezoelectric core-shell nanowires. <i>Nano Letters</i> , 2010 , 10, 1108-12	11.5	101
129	Thermoelectric efficiency at maximum power in low-dimensional systems. <i>Physical Review B</i> , 2010 , 82,	3.3	170
128	Surface-enhanced Raman scattering on dual-layer metallic grating structures. <i>Science Bulletin</i> , 2010 , 55, 2643-2648		8

127	g-factor and exchange energy in a few-electron lateral InGaAs quantum dot. <i>Applied Physics Letters</i> , 2009 , 95, 192112	3.4	8
126	Gate-defined quantum-dot devices realized in InGaAs/InP by incorporating a HfO ₂ layer as gate dielectric. <i>Applied Physics Letters</i> , 2009 , 94, 042114	3.4	17
125	Photoemission electron microscopy using extreme ultraviolet attosecond pulse trains. <i>Review of Scientific Instruments</i> , 2009 , 80, 123703	1.7	62
124	Rectification of spin-bias-induced charge currents. <i>Applied Physics Letters</i> , 2009 , 94, 262103	3.4	3
123	Strain distributions in lattice-mismatched semiconductor core-shell nanowires. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 827		24
122	Spin-3/2 physics of semiconductor hole nanowires: Valence-band mixing and tunable interplay between bulk-material and orbital bound-state spin splittings. <i>Physical Review B</i> , 2009 , 79,	3.3	34
121	Field-driven geometrical phases in a time-periodic quantum system. <i>Physical Review B</i> , 2009 , 79,	3.3	2
120	Giant, level-dependent g factors in InSb nanowire quantum dots. <i>Nano Letters</i> , 2009 , 9, 3151-6	11.5	201
119	Strain in semiconductor core-shell nanowires. <i>Journal of Applied Physics</i> , 2009 , 106, 053508	2.5	62
118	Surface-enhanced Raman scattering of rhodamine 6G on nanowire arrays decorated with gold nanoparticles. <i>Nanotechnology</i> , 2008 , 19, 275712	3.4	50
117	Electrical properties of self-assembled branched InAs nanowire junctions. <i>Nano Letters</i> , 2008 , 8, 1100-4	11.5	50
116	Spin current diode based on an electron waveguide with spin-orbit interaction. <i>Applied Physics Letters</i> , 2008 , 92, 102111	3.4	17
115	Spin states of holes in Ge/Si nanowire quantum dots. <i>Physical Review Letters</i> , 2008 , 101, 186802	7.4	63
114	A Novel SR Latch Device Realized by Integration of Three-Terminal Ballistic Junctions in InGaAs/InP. <i>IEEE Electron Device Letters</i> , 2008 , 29, 540-542	4.4	27
113	Tip-enhanced Raman scattering of p-thiocresol molecules on individual gold nanoparticles. <i>Applied Physics Letters</i> , 2008 , 92, 093110	3.4	28
112	Transport properties of three-terminal ballistic junctions realized by focused ion beam enhanced etching in InGaAs/InP. <i>Applied Physics Letters</i> , 2008 , 93, 133110	3.4	4
111	A sequential logic device realized by integration of in-plane gate transistors in InGaAs/InP. <i>Applied Physics Letters</i> , 2008 , 92, 012116	3.4	6
110	Multiterminal multimode spin-dependent scattering matrix formalism: Electron and hole quantum spin transport in multiterminal junctions. <i>Physical Review B</i> , 2008 , 78,	3.3	4

109	Landlike formula for the g factors of hole-nanowire subband edges. <i>Physical Review B</i> , 2008 , 78,	3.3	12
108	Novel room-temperature functional analogue and digital nanoelectronic circuits based on three-terminal ballistic junctions and planar quantum-wire transistors. <i>Journal of Physics: Conference Series</i> , 2008 , 100, 052073	0.3	2
107	AC Conductance of DNA molecule at low temperature. <i>Journal of Physics: Conference Series</i> , 2008 , 100, 052065	0.3	1
106	Light scattering and plasmon resonances in a metal film with sub-wavelength nano-holes. <i>Journal of Physics: Conference Series</i> , 2008 , 100, 052037	0.3	1
105	Electron transport study of a lateral InGaAs quantum dot. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008 , 40, 1950-1951	3	
104	Electric control of spin polarization orientation in a magnetic-electric barrier structure. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2007 , 369, 498-502	2.3	4
103	Frequency mixing and phase detection functionalities of three-terminal ballistic junctions. <i>Nanotechnology</i> , 2007 , 18, 195205	3.4	29
102	Spin transport and spin Hall effect in an electron waveguide in the presence of an in-plane magnetic field and spin-orbit interaction. <i>Physical Review B</i> , 2007 , 75,	3.3	7
101	Detection of charge states in nanowire quantum dots using a quantum point contact. <i>Applied Physics Letters</i> , 2007 , 90, 172112	3.4	21
100	Spin transport and spin Hall effect in $J = 3/2$ semiconductor systems. <i>Journal of Physics: Conference Series</i> , 2007 , 61, 155-159	0.3	
99	Spin filtering and spin accumulation in an electron stub waveguide with spin-orbit interaction. <i>Physical Review B</i> , 2007 , 76,	3.3	36
98	Coherent electron flow from a double slit with slit widths in the quantum conductance regime. <i>Journal of Physics Condensed Matter</i> , 2006 , 18, 11103-11119	1.8	
97	Spin filtering through magnetic-field-modulated double quantum dot structures. <i>Physical Review B</i> , 2006 , 73,	3.3	7
96	Nonlinear electrical properties of three-terminal junctions. <i>Applied Physics Letters</i> , 2006 , 89, 092124	3.4	48
95	Spin Hall effect and zitterbewegung in an electron waveguide. <i>Physical Review B</i> , 2006 , 74,	3.3	35
94	Symmetry of hole spin transport in a two-terminal quantum system. <i>Physical Review B</i> , 2006 , 74,	3.3	3
93	Nanoimprint lithography for the fabrication of interdigitated cantilever arrays. <i>Nanotechnology</i> , 2006 , 17, 1906-1910	3.4	19
92	Electronic structure of free-standing GaAs/AlGaAs nanowire superlattices. <i>Physical Review B</i> , 2006 , 73,	3.3	24

91	Spin filtering in single magnetic barrier structures revisited. <i>Applied Physics Letters</i> , 2006 , 88, 032502	3-4	40
90	Scattering matrix method for multimode electron transport through quantum wires under a local magnetic field modulation and spin-orbit interaction. <i>Physical Review B</i> , 2006 , 74,	3-3	16
89	Electronic structure of [100]-oriented free-standing InAs and InP nanowires with square and rectangular cross sections. <i>Physical Review B</i> , 2006 , 73,	3-3	31
88	Symmetry of Spin Transport in Two-Terminal Waveguides with a Spin-Orbital Interaction and Magnetic Field Modulations. <i>Physical Review Letters</i> , 2005 , 94,	7-4	179
87	Microwave detection at 110 GHz by nanowires with broken symmetry. <i>Nano Letters</i> , 2005 , 5, 1423-7	11-5	76
86	Multimode electron transport through quantum waveguides with spin-orbit interaction modulation: Applications of the scattering matrix formalism. <i>Physical Review B</i> , 2005 , 72,	3-3	71
85	Generation of spin polarization in two-terminal electron waveguides by spin-orbit interaction and magnetic field modulations. <i>Physical Review B</i> , 2005 , 72,	3-3	24
84	Electrical properties and logic function of multibranch junction structures. <i>Applied Physics Letters</i> , 2005 , 86, 253510	3-4	13
83	Transport through single-channel atomic wires: Effects of connected sites on scattering phase and odd-even parity oscillations. <i>Physical Review B</i> , 2005 , 72,	3-3	7
82	Giant polarization anisotropy in optical transitions of free-standing InP nanowires. <i>Physical Review B</i> , 2004 , 70,	3-3	38
81	Tunable spin polarization in a two-dimensional electron gas modulated by a ferromagnetic metal stripe and a Schottky metal stripe. <i>Physical Review B</i> , 2004 , 70,	3-3	103
80	Novel nanoelectronic triodes and logic devices with TBJs. <i>IEEE Electron Device Letters</i> , 2004 , 25, 164-166	4-4	41
79	Electronic Structure of [100]-Oriented Free-Standing Semiconductor Nanowires. <i>Nano Letters</i> , 2004 , 4, 2409-2414	11-5	33
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